

General Description

The MY40P03D uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

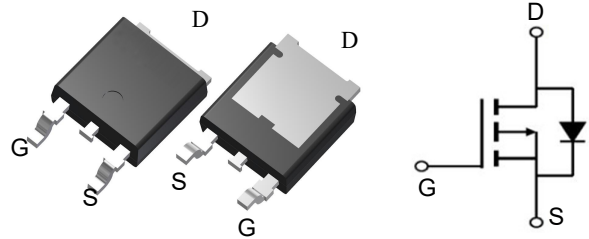


Features

V_{DSS}	-30	V
I_D	-40	A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	18	$m\Omega$
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	25	$m\Omega$

Application

- Battery protection
- Load switch
- Uninterruptible power supply



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY40P03D	TO-252-2L	MY40P03D	2500

Absolute Maximum Ratings ($T_A=25\text{ }^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating		Units
		10s	Steady State	
V_{DS}	Drain-Source Voltage	-30		V
V_{GS}	Gate-Source Voltage	± 20		V
$I_D@T_C=25\text{ }^\circ\text{C}$	Continuous Drain Current, V_{GS} @ -10V ¹	-40		A
$I_D@T_C=100\text{ }^\circ\text{C}$	Continuous Drain Current, V_{GS} @ -10V ¹	-22		A
$I_D@T_A=25\text{ }^\circ\text{C}$	Continuous Drain Current, V_{GS} @ -10V ¹	-13.4	-8.5	A
$I_D@T_A=70\text{ }^\circ\text{C}$	Continuous Drain Current, V_{GS} @ -10V ¹	-10.7	-6.8	A
I_{DM}	Pulsed Drain Current ²	-70		A
EAS	Single Pulse Avalanche Energy ³	72.2		mJ
I_{AS}	Avalanche Current	-38		A
$P_D@T_C=25\text{ }^\circ\text{C}$	Total Power Dissipation ⁴	37.7		W
$P_D@T_A=25\text{ }^\circ\text{C}$	Total Power Dissipation ⁴	5	2.0	W
T_{STG}	Storage Temperature Range	-55 to 150		$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150		$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ ($t \leq 10s$)	---	25	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	3.6	$^\circ\text{C/W}$

Electrical Characteristics (T_A=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-30	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.022	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-15A	---	18	20	mΩ
		V _{GS} =-4.5V, I _D =-10A	---	25	32	
V _{GS(th)}	Gate Threshold Voltage		-1.0	---	-2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient	V _{GS} =V _{DS} , I _D =-250μA	---	4.6	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-24V, V _{GS} =0V, T _J =25°C	---	---	-1	μA
		V _{DS} =-24V, V _{GS} =0V, T _J =55°C	---	---	-5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-10A	---	5	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	13	---	Ω
Q _g	Total Gate Charge (-4.5V)		---	12.5	---	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-15V, V _{GS} =-4.5V, I _D =-15A	---	5.4	---	
Q _{gd}	Gate-Drain Charge		---	5	---	
T _{d(on)}	Turn-On Delay Time		---	4.4	---	ns
T _r	Rise Time	V _{DD} =-15V, V _{GS} =-10V, R _G =3.3Ω, I _D =-15A	---	11.2	---	
T _{d(off)}	Turn-Off Delay Time		---	34	---	
T _f	Fall Time		---	18	---	
C _{iss}	Input Capacitance		---	1345	---	pF
C _{oss}	Output Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	194	---	
C _{rss}	Reverse Transfer Capacitance		---	158	---	
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	-35	A
I _{SM}	Pulsed Source Current ^{2,5}		---	---	-70	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V
t _{rr}	Reverse Recovery Time	I _F =-15A, dI/dt=100A/μs, T _J =25°C	---	12.4	---	nS
Q _{rr}	Reverse Recovery Charge		---	5	---	nC

Typical Characteristics

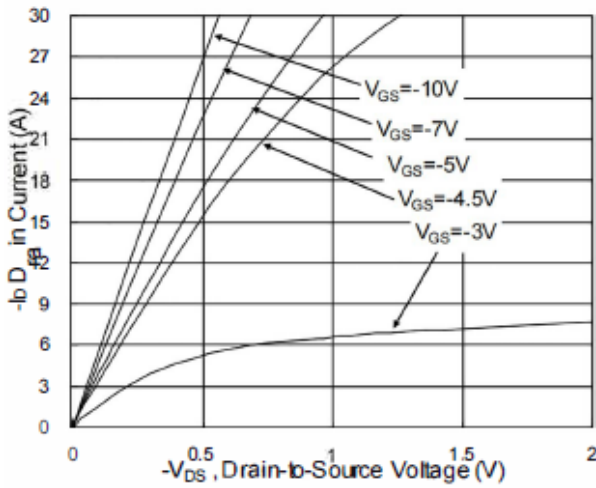


Fig.1 Typical Output Characteristics

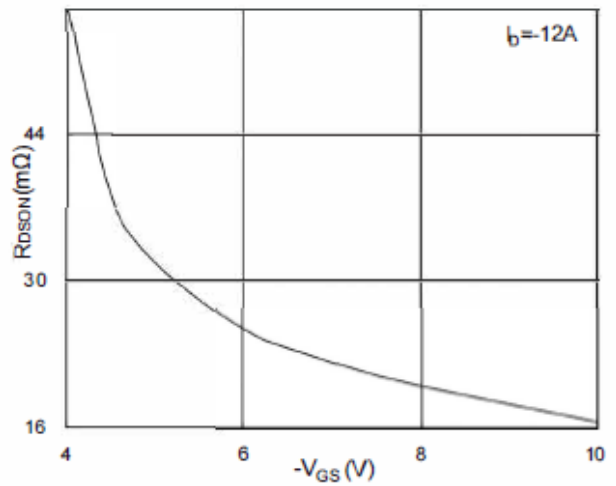


Fig.2 On-Resistance v.s Gate-Source

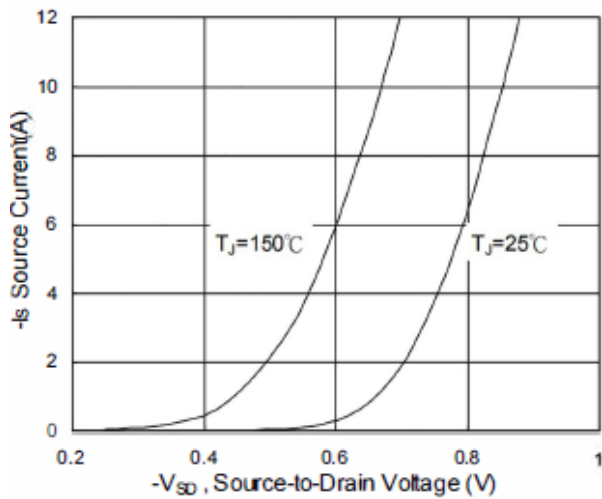


Fig.3 Forward Characteristics of Reverse

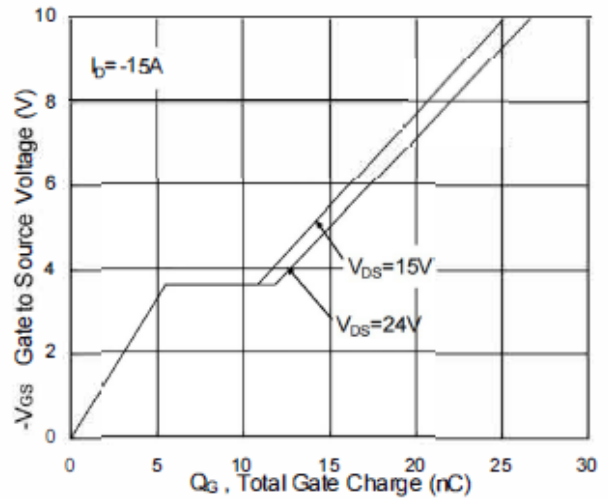


Fig.4 Gate-Charge Characteristics

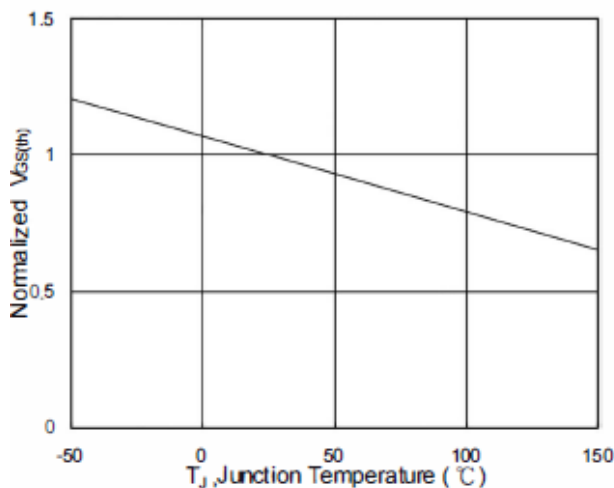


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

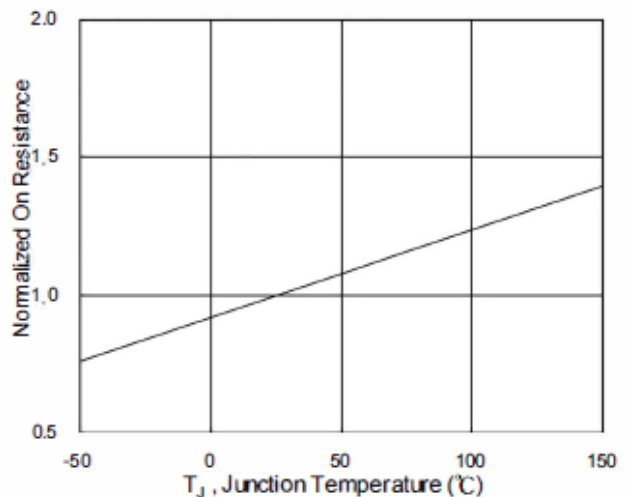


Fig.6 Normalized $R_{DS(on)}$ v.s T_J

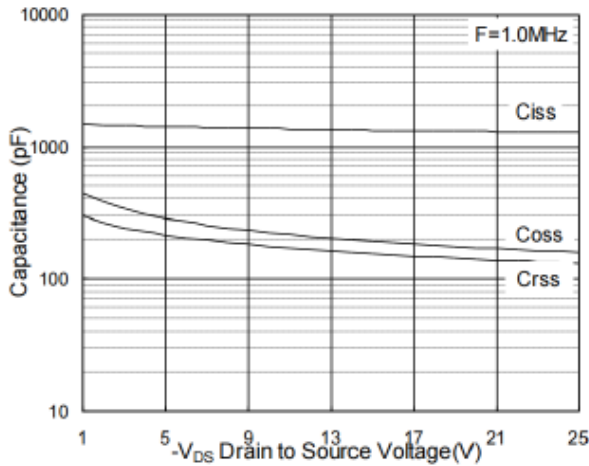


Fig.7 Capacitance

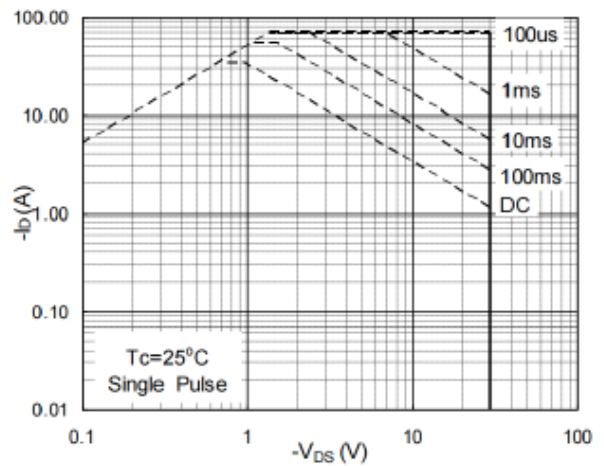


Fig.8 Safe Operating Area

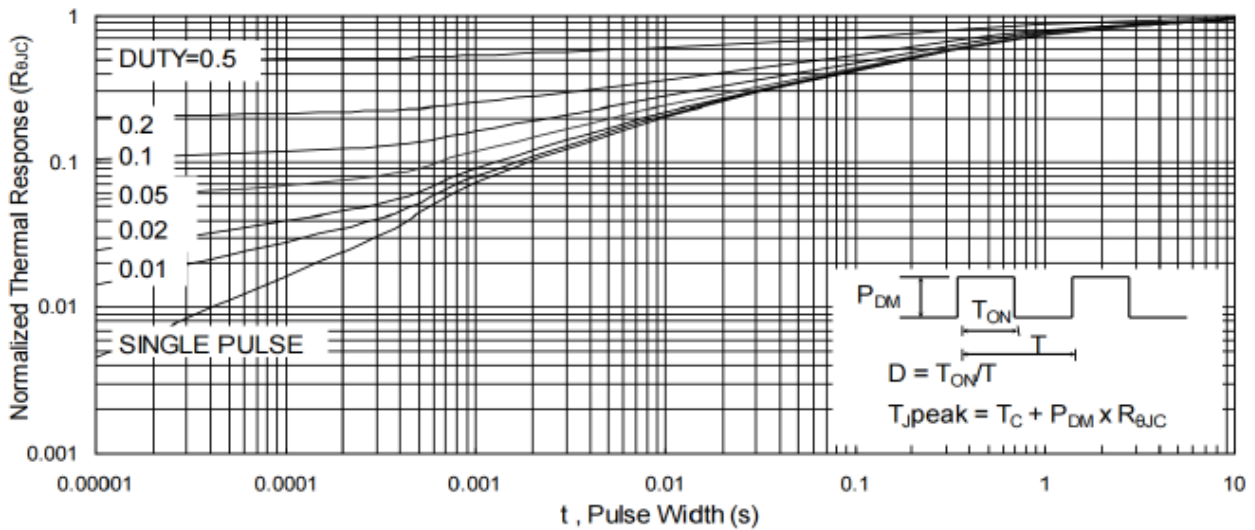


Fig.9 Normalized Maximum Transient Thermal Impedance

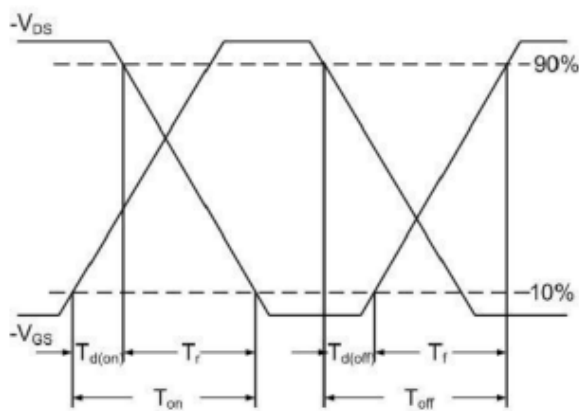


Fig.10 Switching Time Waveform

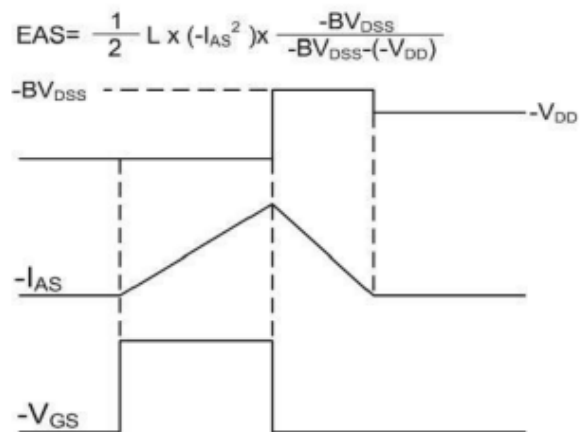
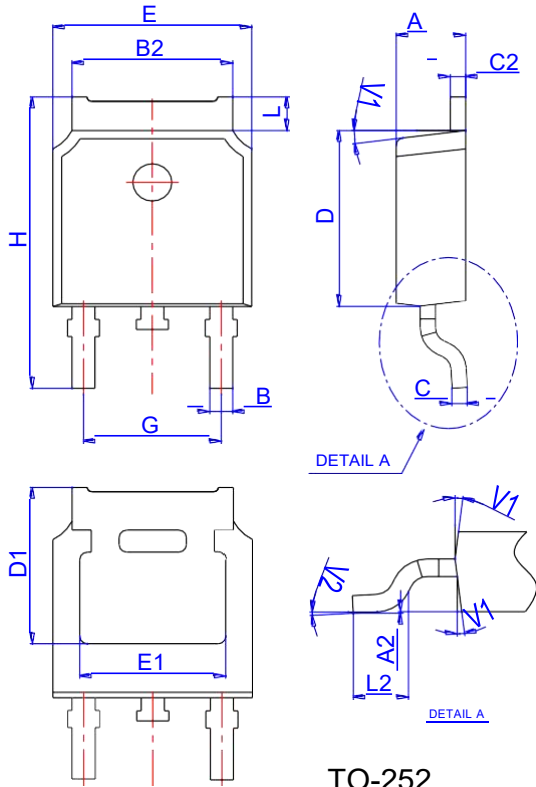


Fig.11 Unclamped Inductive Switching Waveform

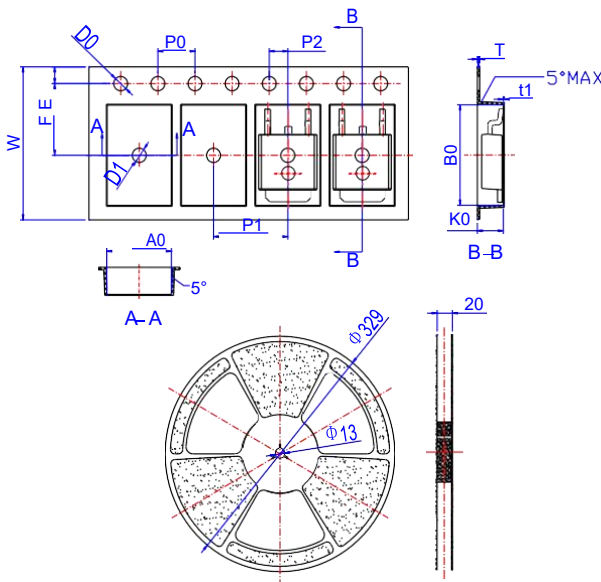
Package Mechanical Data-TO-252-JQ Single



TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2		0°	6°		0°	6°

Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583